WHAT IS CLAIMED IS:

- 1 1. A dielectric substrate having a multiturn inductor comprising:
- a) a multilayer dielectric body comprising a plurality of layers;
- 3 b) a multiturn inductor buried within the dielectric body, each
- 4 turn of the inductor comprising a bottom portion, a top portion and
- 5 two side portions, the bottom portion and top portion being
- 6 parallel and in different layers of the dielectric body, the side
 - portions being parallel to each other and extending between the top
 - and bottom portions and comprising vias in the dielectric body.
 - 2. The dielectric substrate of claim 1 wherein the top and bottom portions comprise lines situated in respective layers of the dielectric body.
- 1 3. The dielectric substrate of claim 2 wherein the top and bottom
- 2 portions each comprise two parallel lines in juxtaposition.
- 1 4. The dielectric substrate of claim 3 further comprising vias
- 2 connecting the parallel lines of each of the top and bottom
- 3 portions.

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- 1 5. The dielectric substrate of claim 4 wherein the vias connecting
- 2 the parallel lines are only at the ends of the lines.
- 1 6. The dielectric substrate of claim 4 wherein the vias connecting
- 2 the parallel lines are spaced along the length of the lines.
- 7. The dielectric substrate of claim 1 wherein the turns of the multiturn inductor form a toroidal shape.
 - 8. The dielectric substrate of claim 1 wherein the multiturn inductor is tunable by tapping the multiturn inductor at selected locations.
- 1 9. The dielectric substrate of claim 8 further comprising deleting
- a portion of the multiturn inductor.
- 1 10. The dielectric substrate of claim 1 wherein the multiturn
- 2 inductor is tunable by adding at least one additional buried loop
- 3 to the multiturn inductor.

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- 1 11. The dielectric substrate of claim 1 wherein the multiturn
- 2 inductor is tunable by adding a plate adjacent to the multiturn
- 3 inductor, the plate being electrically isolated from the multiturn
- 4 inductor.
- 1 12. The dielectric substrate of claim 1 wherein the multiturn
- 2 inductor is tunable by adding a plate adjacent to the multiturn
- 3 inductor, the plate being electrically connected to the multiturn
- 4 inductor.
 - 13. The dielectric substrate of claim 1 wherein the multiturn inductor is a first multiturn inductor and further comprising a second buried multiturn inductor near the first multiturn inductor but electrically isolated therefrom, the first and second multiturn inductors cooperating to form a transformer.
- 1 14. A method of forming a dielectric substrate having a multiturn
- 2 inductor, the method comprising the steps of:
- 3 a) obtaining a plurality of layers;
- 4 b) forming conductive lines on a first group of layers;

- 5 c) forming conductive vias in a second group of layers;
- 6 d) forming conductive lines on a third group of layers;
- 7 e) stacking at least one layer from the second group of layers on
- 8 at least one layer from the third group of layers; and
- 9 f) stacking at least one layer from the first group of layers on
- 10 the at least one layer from the second group of layers wherein the
- 11 stacking of the first, second and third groups of layers form an
- 12 inductor buried within a dielectric substrate.
 - 15. The method of claim 14 wherein the respective layers are greensheets and the inductor and dielectric substrate are unsintered and further comprising the step of: g) sintering the unsintered dielectric substrate having an unsintered inductor buried therein to form a dielectric substrate having a multiturn inductor buried therein.
 - 1 16. The method of claim 14 wherein there are a plurality of layers
 - 2 from each of the first and third group of layers.
 - 1 17. The method of claim 14 wherein there are a plurality of layers
 - 2 from the second group of layers.

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- 1 18. The method of claim 14 wherein the vias in the second group of
- layers contact the conductive lines in the first and third group of
- 3 layers only at the ends of the conductive lines.
- 1 19. The method of claim 14 wherein the vias in the second group of
- 2 layers contact the conductive lines in the first and third group of
- 3 layers along the length of the conductive lines.
 - 20. The method of claim 14 wherein the multiturn inductor is in the form of a toroidal shape.